



T-33-05

Silicon NPN Epitaxial Planar RF Transistor

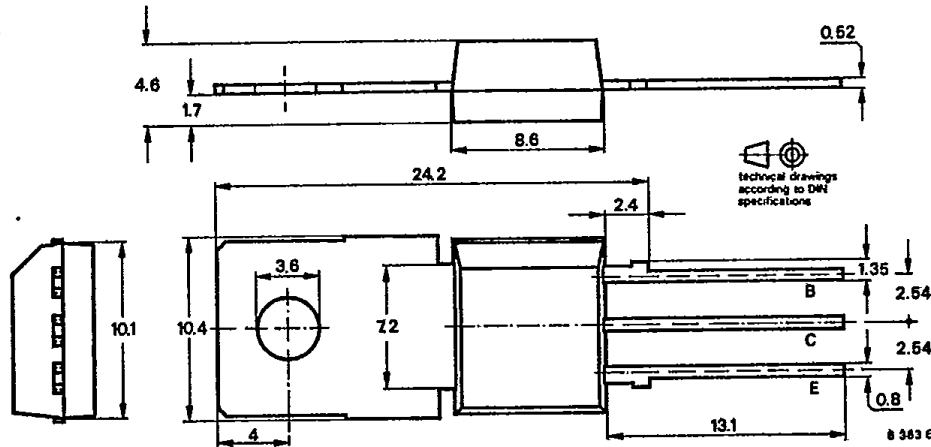
Applications: Video B-class power stages in TV receivers

Features:

● High reverse voltage

● No h_{FE} -drift dependent of temperature

Dimensions in mm



Standard plastic case
34 A 3 DIN 41 869
JEDEC TO 202
Weight max. 1.8 g

Collector connected with metallic surface

Absolute maximum ratings

Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	275	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector peak current	I_{CM}	300	mA
Total power dissipation $T_{case} \leq 25^\circ C$	P_{tot}	7	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	-65 ... +150	$^\circ C$

Maximum thermal resistances

Junction ambient	R_{thJA}	78	K/W
Junction case	R_{thJC}	17.8	K/W

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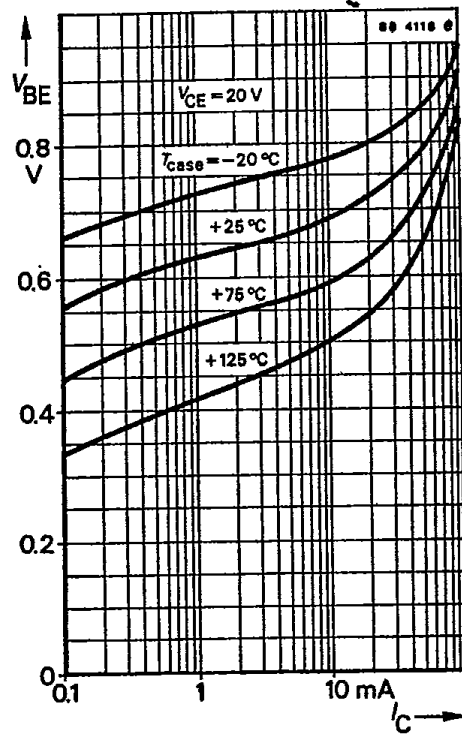
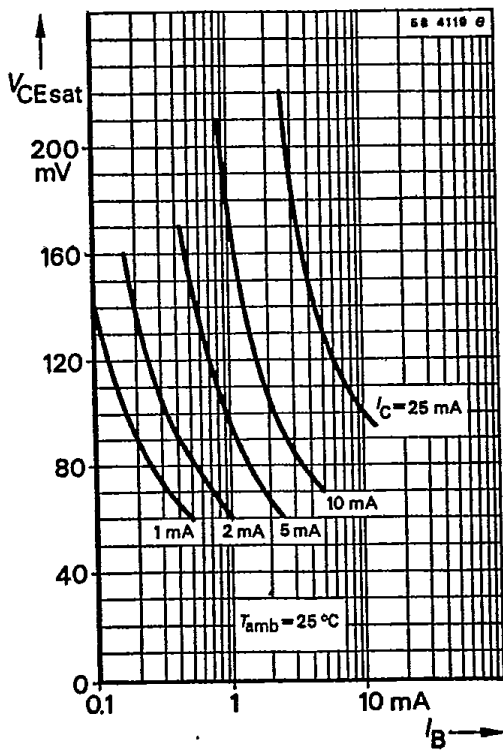
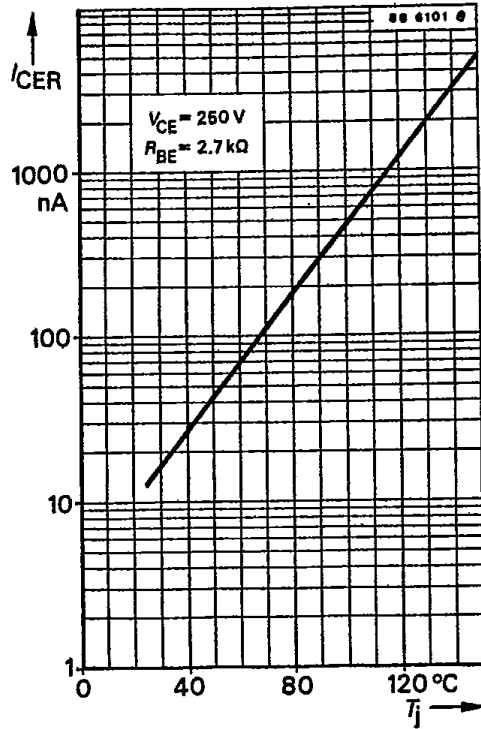
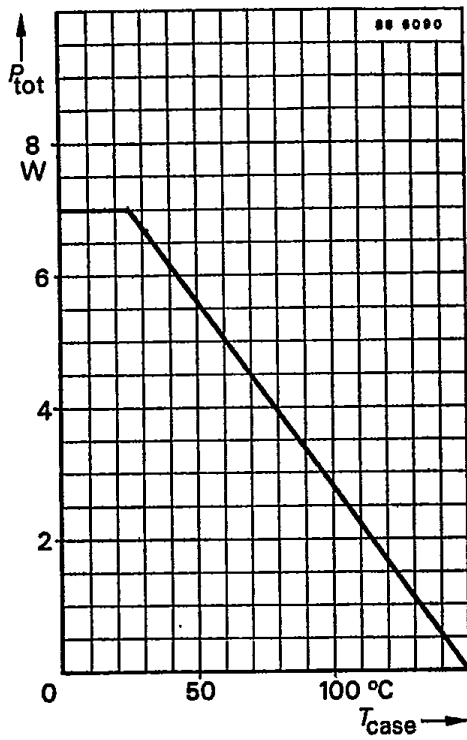
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Characteristics		Min.	Typ.	Max.
$T_{amb} = 25^\circ C$, unless otherwise specified				
Collector cut-off current				
$V_{CE} = 250 V, R_{BE} = 2.7 k\Omega$	I_{CER}			50 nA
$V_{CE} = 200 V, R_{BE} = 2.7 k\Omega, T_J = 150^\circ C$	I_{CER}			10 μA
Emitter cut-off current				
$V_{EB} = 5 V$	I_{EBO}			10 μA
Collector-emitter breakdown voltage				
$I_C = 1 mA$	$V_{(BR)CEO}$	275		V
$I_C = 1 \mu A, R_{BE} = 2.7 k\Omega$	$V_{(BR)CER}$	300		V
DC forward current transfer ratio				
$V_{CE} = 20 V, I_C = 25 mA$	h_{FE}	50		
Gain bandwidth product				
$V_{CE} = 10 V, I_C = 10 mA$	f_T	60	90	MHz
Feedback capacitance				
$V_{CE} = 30 V, I_C = 1 mA, f = 1 MHz$	C_{12e}		1.2	1.8 pF
Collector saturation RF voltage				
$I_C = 25 mA, T_J = 150^\circ C$	$V_{CEsatHF}$		20	V

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